

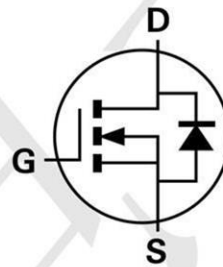
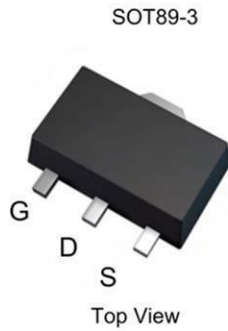
Features

- $V_{DS} = 60V, I_D = 3.5A$
 $R_{DS(ON)} < 100m\Omega @ V_{GS} = 10V$
 $R_{DS(ON)} < 120m\Omega @ V_{GS} = 4.5V$
- High Power and current handling capability
- Lead free product is acquired
- Surface mount package

Application

- Load/Power Switching
- Interfacing Switching
- Battery Management for Ultra Small Portable Electronics
- Logic Level Shift

Package and Pin Configuration



Marking:  603N

Absolute Maximum Ratings ($T_A = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	3.5	A
Drain Current-Pulsed ^(Note 1)	I_{DM}	10	A
Maximum Power Dissipation	P_D	1.7	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^\circ C$

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient ^(Note 2)	$R_{\theta JA}$	73.5	$^\circ C/W$
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Electrical Characteristics (T_A=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	60	-		V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V, V _{GS} =0V	-	-	1	μA
Parameter						
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1		2.3	V
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =10V, I _D =3A	-	62		mΩ
		V _{GS} =4.5V, I _D =3A	-	-	120	mΩ
Forward Transconductance	g _{FS}	V _{DS} =15V, I _D =2A	2	-	-	S
Dynamic Characteristics (Note 4)						
Input Capacitance	C _{iss}	V _{DS} =30V, V _{GS} =0V, F=1.0MHz	-	247	-	PF
Output Capacitance	C _{oss}		-	34	-	PF
Reverse Transfer Capacitance	C _{rss}		-	19.5	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =30V, I _D =1.5A V _{GS} =10V, R _{GEN} =1Ω	-	6	-	nS
Turn-on Rise Time	t _r		-	15	-	nS
Turn-Off Delay Time	t _{d(off)}		-	15	-	nS
Turn-Off Fall Time	t _f		-	10	-	nS
Total Gate Charge	Q _g	V _{DS} =30V, I _D =3A, V _{GS} =4.5V	-	6	-	nC
Gate-Source Charge	Q _{gs}		-	1	-	nC
Gate-Drain Charge	Q _{gd}		-	1.3	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V, I _S =3A	-	-	1.2	V
Diode Forward Current (Note 2)	I _S		-	-	3	A

Typical Characteristics

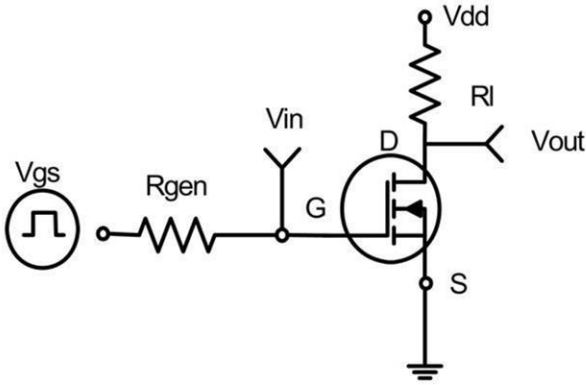


Figure 1 Switching Test Circuit

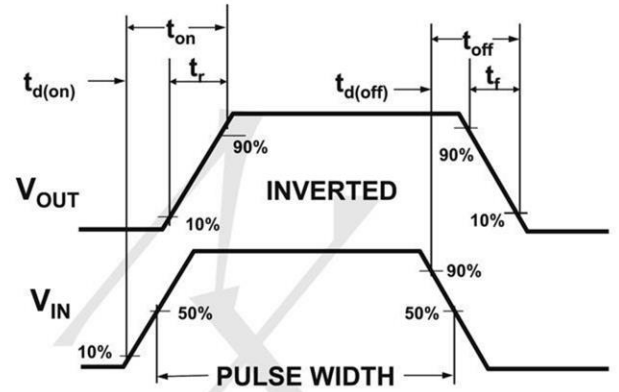


Figure 2 Switching Waveforms

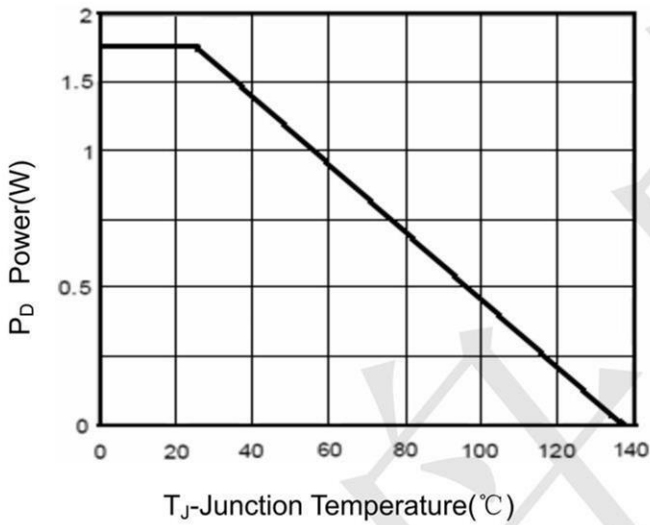


Figure 3 Power Dissipation

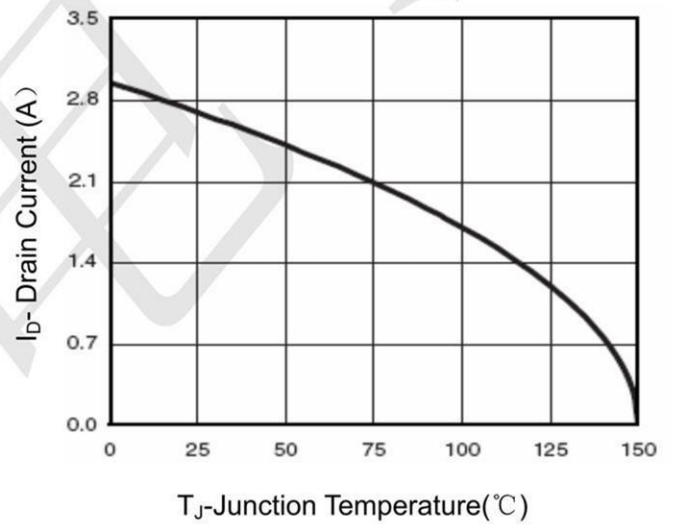


Figure 4 Drain Current

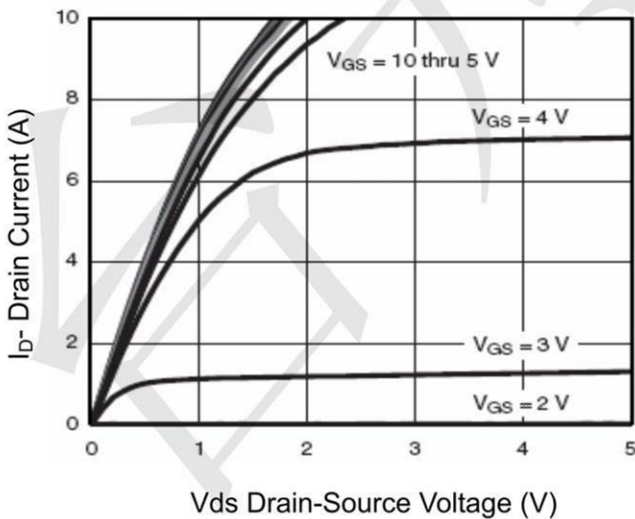


Figure 5 Output Characteristics

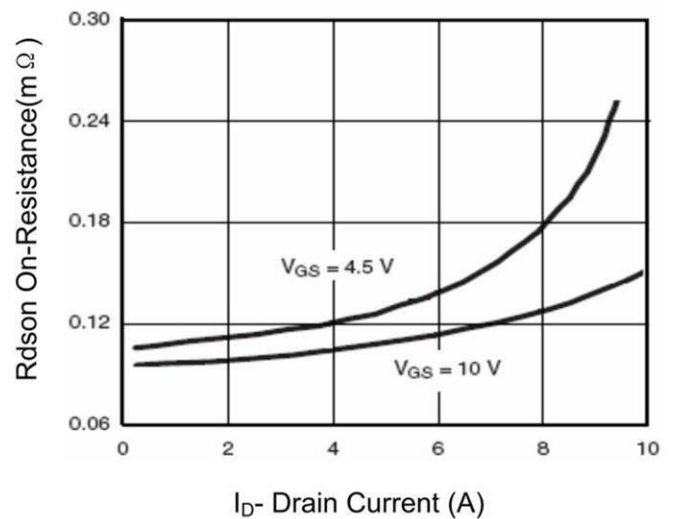
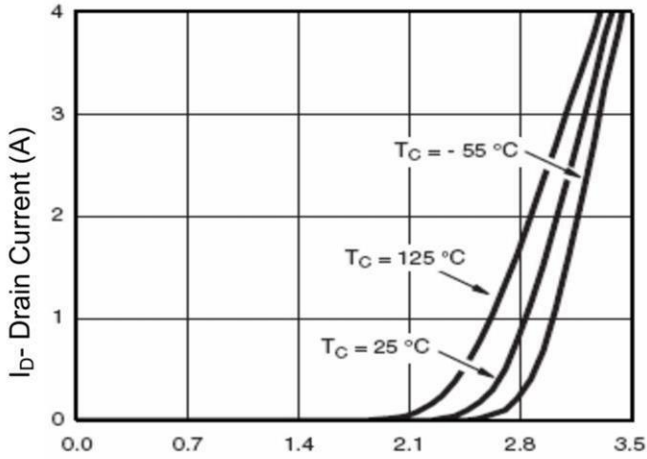
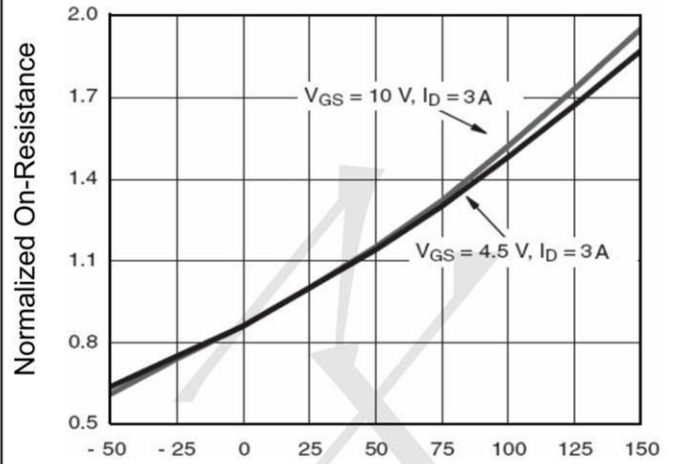


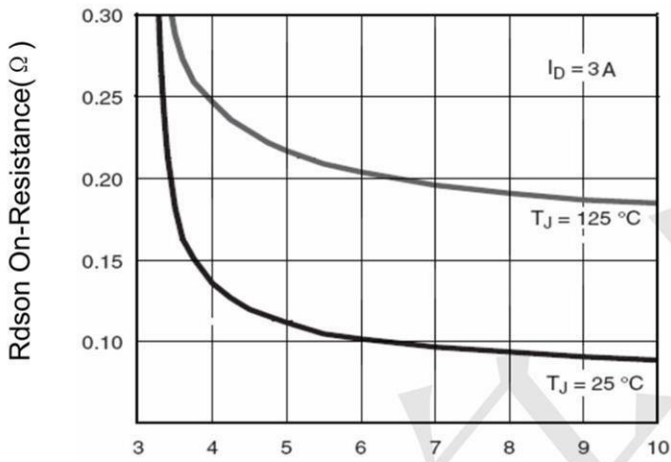
Figure 6 Drain-Source On-Resistance



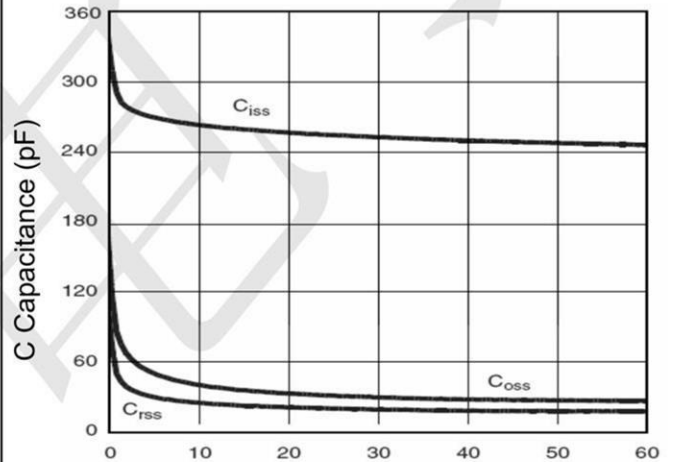
Vgs Gate-Source Voltage (V)
Figure 7 Transfer Characteristics



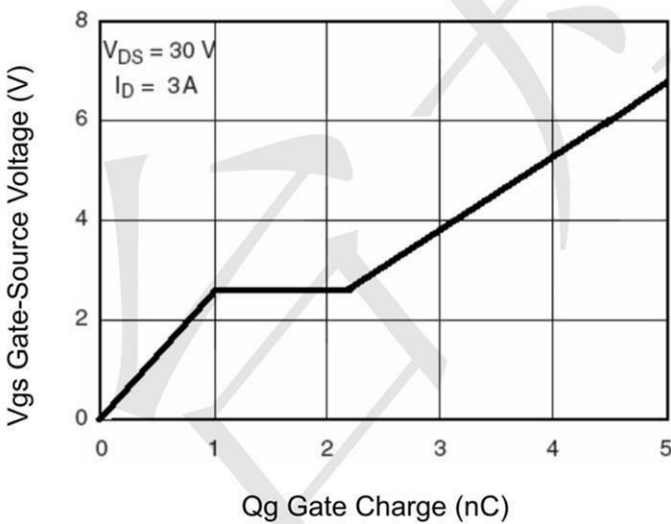
T_J -Junction Temperature($^\circ\text{C}$)
Figure 8 Drain-Source On-Resistance



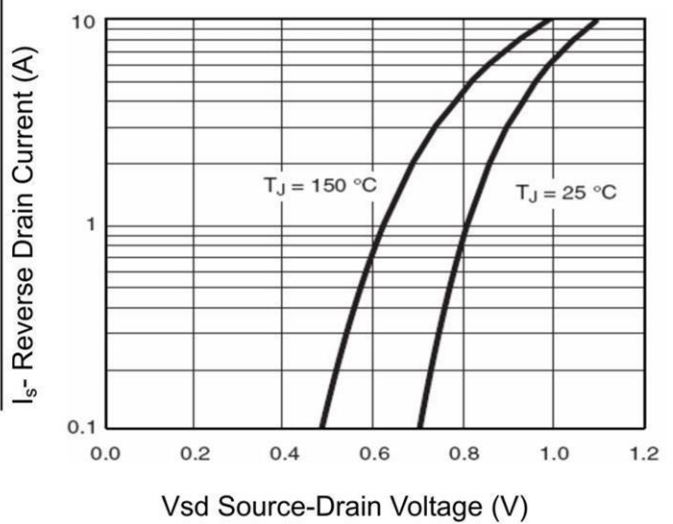
Vgs Gate-Source Voltage (V)
Figure 9 Rdson vs Vgs



Vds Drain-Source Voltage (V)
Figure 10 Capacitance vs Vds



Q_g Gate Charge (nC)
Figure 11 Gate Charge



Vsd Source-Drain Voltage (V)
Figure 12 Source- Drain Diode Forward

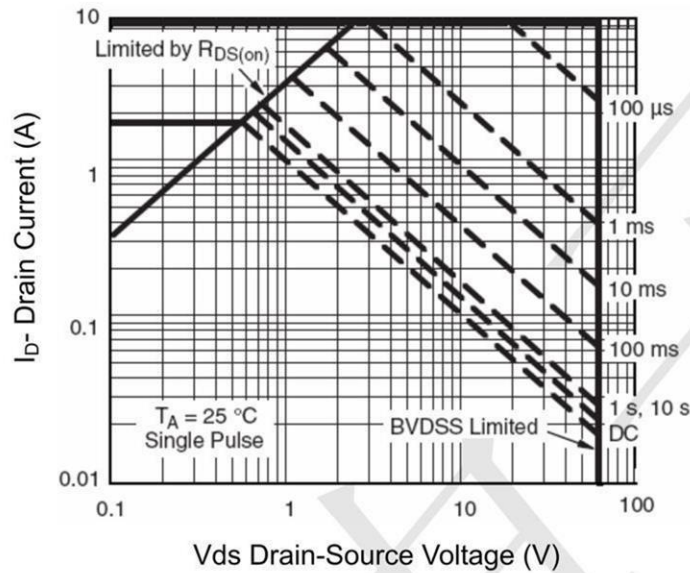


Figure 13 Safe Operation Area

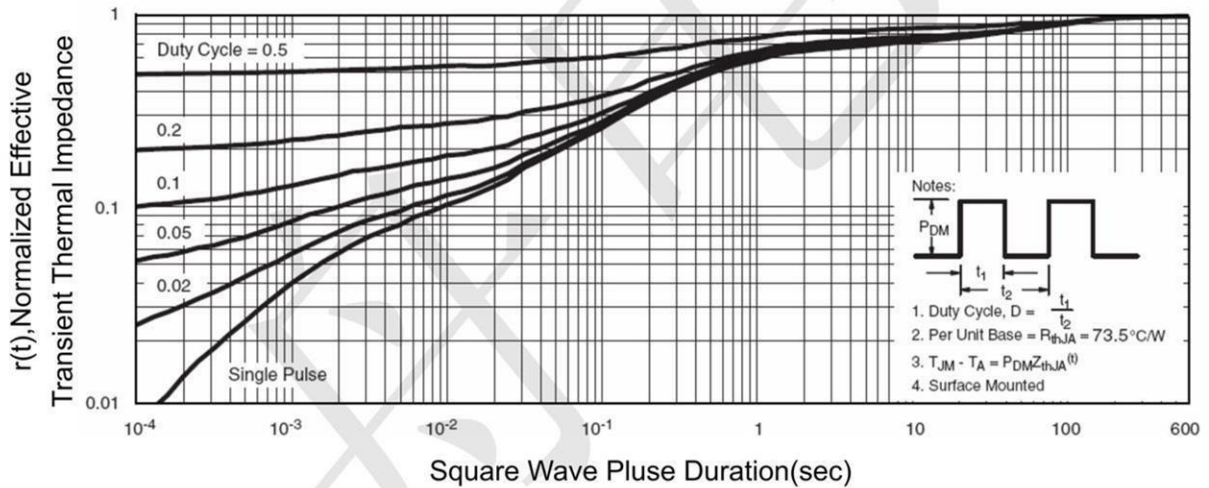
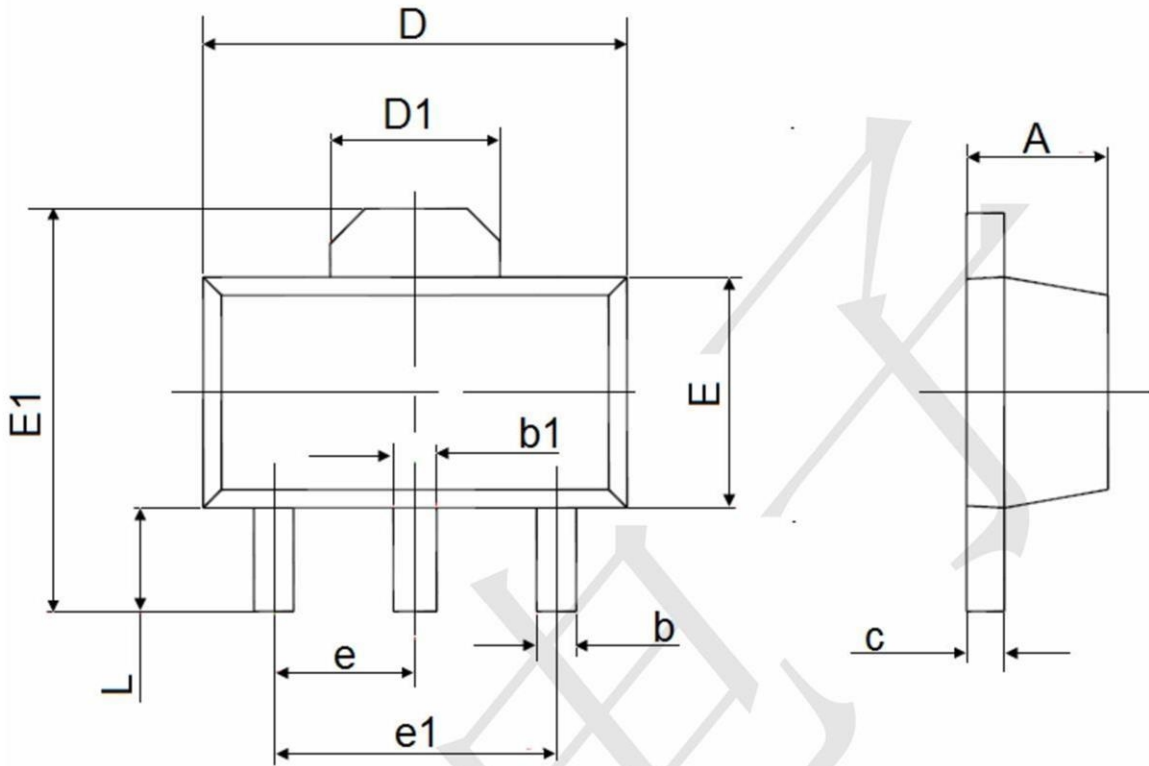


Figure 14 Normalized Maximum Transient Thermal Impedance

SOT-89-3L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.400	1.600	0.055	0.063
b	0.320	0.520	0.013	0.020
b1	0.400	0.580	0.016	0.023
c	0.350	0.440	0.014	0.017
D	4.400	4.600	0.173	0.181
D1	1.550 REF.		0.061 REF.	
E	2.300	2.600	0.091	0.102
E1	3.940	4.250	0.155	0.167
e	1.500 TYP.		0.060 TYP.	
e1	3.000 TYP.		0.118 TYP.	
L	0.900	1.200	0.035	0.047